

UNITED STATES PATENT AND TRADEMARK OFFICE
CERTIFICATE OF CORRECTION

PATENT NO. : 7,144,795 B1
APPLICATION NO. : 10/729491
DATED : December 5, 2006
INVENTOR(S) : Lines

Page 1 of 1

It is certified that error appears in the above-identified patent and that said Letters Patent is hereby corrected as shown below:

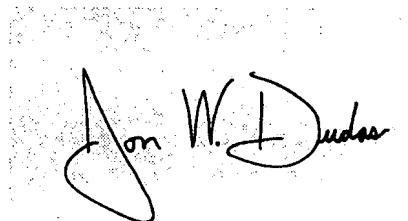
Column 1, Line 13,

After "Field of the Invention", insert new paragraph

--The present invention relates to depletion-mode transistors and, more particularly, to a method of forming a depletion-mode transistor that eliminates the need to separately set the threshold voltage of the depletion-mode transistor.--

Signed and Sealed this

Twenty-second Day of May, 2007



JON W. DUDAS
Director of the United States Patent and Trademark Office